

Mingchu Tang

List of Publications by Year in descending order

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107
papers

2,892
citations

201674

27
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175258

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107
all docs

107
docs citations

107
times ranked

2290
citing authors

#	ARTICLE	IF	CITATIONS
1	Single-Mode Photonic Crystal Nanobeam Lasers Monolithically Grown on Si for Dense Integration. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-6.	2.9	4
2	Multi-wavelength 128 Gbit/s $\times 1$ PAM4 optical transmission enabled by a 100 GHz quantum dot mode-locked optical frequency comb. Journal Physics D: Applied Physics, 2022, 55, 144001.	2.8	8
3	Recent Progress of Quantum Dot Lasers Monolithically Integrated on Si Platform. Frontiers in Physics, 2022, 10, .	2.1	14
4	The role of different types of dopants in 1.3 μ m InAs/GaAs quantum-dot lasers. Journal Physics D: Applied Physics, 2022, 55, 215105.	2.8	6
5	Refractive indices of MBE-grown Al _x Ga(1-x)As ternary alloys in the transparent wavelength region. AIP Advances, 2021, 11, .	1.3	52
6	Co-Package Technology Platform for Low-Power and Low-Cost Data Centers. Applied Sciences (Switzerland), 2021, 11, 6098.	2.5	6
7	Microcavity lasers directly grown on silicon. , 2021, , .		0
8	All-MBE grown InAs/GaAs quantum dot lasers with thin Ge buffer layer on Si substrates. Journal Physics D: Applied Physics, 2021, 54, 035103.	2.8	23
9	Monolithic III-V quantum dot lasers on silicon. Frontiers of Nanoscience, 2021, 20, 353-388.	0.6	3
10	Various microcavity lasers monolithically grown on planar on-axis Si (001) substrates. , 2021, , .		0
11	The limits to peak modal gain in p-modulation doped indium arsenide quantum dot laser diodes. , 2021, , .		0
12	Origin of Defect Tolerance in InAs/GaAs Quantum Dot Lasers Grown on Silicon. Journal of Lightwave Technology, 2020, 38, 240-248.	4.6	46
13	Inversion Boundary Annihilation in GaAs Monolithically Grown on On-axis Silicon (001). Advanced Optical Materials, 2020, 8, 2000970.	7.3	22
14	Theoretical Study on the Effects of Dislocations in Monolithic III-V Lasers on Silicon. Journal of Lightwave Technology, 2020, 38, 4801-4807.	4.6	15
15	Continuous-wave quantum dot photonic crystal lasers grown on on-axis Si (001). Nature Communications, 2020, 11, 977.	12.8	61
16	Impact of ex-situ annealing on strain and composition of MBE grown GeSn. Journal Physics D: Applied Physics, 2020, 53, 485104.	2.8	4
17	Quantum dot mode-locked frequency comb with ultra-stable 25.5 GHz spacing between 20°C and 120°C. Photonics Research, 2020, 8, 1937.	7.0	14
18	Heteroepitaxial Growth of III-V Semiconductors on Silicon. Crystals, 2020, 10, 1163.	2.2	56

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19	InAs/GaAs Quantum Dot Microlasers Formed on Silicon Using Monolithic and Hybrid Integration Methods. <i>Materials</i> , 2020, 13, 2315.	2.9	14
20	Photonic crystal lasers grown on CMOS-compatible on-axis Si(001). , 2020, , .		0
21	Electrically pumped continuous-wave O-band quantum-dot superluminescent diode on silicon. <i>Optics Letters</i> , 2020, 45, 5468.	3.3	4
22	III-V quantum dot lasers epitaxially grown on Si substrates. , 2019, , 17-39.		3
23	Recent progress in epitaxial growth of III-V quantum-dot lasers on silicon substrate. <i>Journal of Semiconductors</i> , 2019, 40, 101302.	3.7	29
24	Investigation into the current loss in InAs/GaAs quantum dot solar cells with Si-doped quantum dots. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 505108.	2.8	0
25	InAs/GaAs quantum dot solar cells with quantum dots in the base region. <i>IET Optoelectronics</i> , 2019, 13, 215-217.	3.3	9
26	Stabilization of GaAs photoanodes by <i>in situ</i> deposition of nickel-borate surface catalysts as hole trapping sites. <i>Sustainable Energy and Fuels</i> , 2019, 3, 814-822.	4.9	14
27	Integration of III-V lasers on Si for Si photonics. <i>Progress in Quantum Electronics</i> , 2019, 66, 1-18.	7.0	86
28	Selective area intermixing of III-V quantum-dot lasers grown on silicon with two wavelength lasing emissions. <i>Semiconductor Science and Technology</i> , 2019, 34, 085004.	2.0	4
29	Degradation of III-V Quantum Dot Lasers Grown Directly on Silicon Substrates. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2019, 25, 1-6.	2.9	10
30	The effect of post-growth rapid thermal annealing on InAs/InGaAs dot-in-a-well structure monolithically grown on Si. <i>Journal of Applied Physics</i> , 2019, 125, 135301.	2.5	5
31	Thin Ge buffer layer on silicon for integration of III-V on silicon. <i>Journal of Crystal Growth</i> , 2019, 514, 109-113.	1.5	17
32	O-band InAs/GaAs quantum dot laser monolithically integrated on exact (001) Si substrate. <i>Journal of Crystal Growth</i> , 2019, 511, 56-60.	1.5	31
33	Optically-pumped InAs/GaAs quantum-dot microdisk lasers monolithically grown on on-axis Si (001) substrate. , 2019, , .		1
34	High performance waveguide uni-travelling carrier photodiode grown by solid source molecular beam epitaxy. <i>Optics Express</i> , 2019, 27, 37065.	3.4	12
35	Roadmap of 1300-nm InAs/GaAs quantum dot laser grown on silicon for silicon photonics. , 2019, , .		7
36	III-V Quantum Dot Lasers Monolithically Grown on Silicon. , 2019, , .		3

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37	Ultra-low threshold InAs/GaAs quantum dot microdisk lasers on planar on-axis Si (001) substrates. <i>Optica</i> , 2019, 6, 430.	9.3	37
38	Elevated temperature lasing from injection microdisk lasers on silicon. <i>Laser Physics Letters</i> , 2018, 15, 015802.	1.4	14
39	Direct growth of InAs/GaSb type II superlattice photodiodes on silicon substrates. <i>IET Optoelectronics</i> , 2018, 12, 2-4.	3.3	16
40	Type-II InAs/GaAsSb Quantum Dot Solar Cells With GaAs Interlayer. <i>IEEE Journal of Photovoltaics</i> , 2018, 8, 741-745.	2.5	22
41	InAs/GaAs Quantum Dot Lasers Monolithically Integrated on Group IV Platform. , 2018, , .		1
42	Degradation Studies of InAs / GaAs QD Lasers Grown on Si. , 2018, , .		1
43	Increasing Maximum Gain in InAs Quantum Dot Lasers on GaAs and Si. , 2018, , .		0
44	The influence of direct, delta, and modulation QD Si doping on InAs/GaAs quantum dot solar cells. , 2018, , .		1
45	Optimization of 1.3 μm InAs/GaAs quantum dot lasers epitaxially grown on silicon: taking the optical loss of metamorphic epilayers into account. <i>Laser Physics</i> , 2018, 28, 126206.	1.2	5
46	Hybrid III-V/IV Nanowires: High-Quality Ge Shell Epitaxy on GaAs Cores. <i>Nano Letters</i> , 2018, 18, 6397-6403.	9.1	6
47	Physics-Based Modeling and Experimental Study of Si-Doped InAs/GaAs Quantum Dot Solar Cells. <i>International Journal of Photoenergy</i> , 2018, 2018, 1-10.	2.5	13
48	Monolithic quantum-dot distributed feedback laser array on silicon. <i>Optica</i> , 2018, 5, 528.	9.3	85
49	Two-colour In _{0.5} Ga _{0.5} As quantum dot infrared photodetectors on silicon. <i>Semiconductor Science and Technology</i> , 2018, 33, 094009.	2.0	21
50	Effect of rapid thermal annealing on threading dislocation density in III-V epilayers monolithically grown on silicon. <i>Journal of Applied Physics</i> , 2018, 123, .	2.5	12
51	Low-noise 1.3 μm InAs/GaAs quantum dot laser monolithically grown on silicon. <i>Photonics Research</i> , 2018, 6, 1062.	7.0	35
52	O-band InAs Quantum Dot Light Sources Monolithically Grown on Si. , 2018, , .		0
53	Integrating III-V quantum dot lasers on silicon substrates for silicon photonics. , 2017, , .		0
54	Monolithically Integrated Electrically Pumped Continuous-Wave III-V Quantum Dot Light Sources on Silicon. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2017, 23, 1-10.	2.9	28

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55	Silicon-Based Single Quantum Dot Emission in the Telecoms C-Band. ACS Photonics, 2017, 4, 1740-1746.	6.6	10
56	Influence of Si doping on InAs/GaAs quantum dot solar cells with AlAs cap layers. , 2017, , .		0
57	Influence of built-in charge on photogeneration and recombination processes in InAs/GaAs quantum dot solar cells. Journal Physics D: Applied Physics, 2017, 50, 165101.	2.8	5
58	Impact of the growth temperature on the performance of 1.70-eV Al _{0.22} Ga _{0.78} As solar cells grown by MBE. Journal of Crystal Growth, 2017, 475, 322-327.	1.5	2
59	Si-Doped InAs/GaAs Quantum Dot Solar Cell with AlAs Cap Layers. E3S Web of Conferences, 2017, 16, 16001.	0.5	2
60	III-IV quantum dot lasers epitaxially grown on Si. , 2017, , .		1
61	Electrically pumped continuous-wave 13 μm InAs/GaAs quantum dot lasers monolithically grown on on-axis Si (001) substrates. Optics Express, 2017, 25, 4632.	3.4	102
62	High-performance InAs/GaAs quantum-dot laser diodes monolithically grown on silicon for silicon photonics. , 2017, , .		0
63	Heat-sink free CW operation of injection microdisk lasers grown on Si substrate with emission wavelength beyond 13 μm . Optics Letters, 2017, 42, 3319.	3.3	40
64	MBE growth of 1.7eV Al _{0.2} Ga _{0.8} As and 1.42eV GaAs solar cells on Si using dislocations filters: an alternative pathway toward III-V/ Si solar cells architectures. , 2017, , .		0
65	Long lifetime quantum-dot laser monolithically grown on silicon. , 2016, , .		1
66	Deep-etched III-V lasers grown directly on silicon substrates. , 2016, , .		0
67	1.7eV Al _{0.2} Ga _{0.8} As solar cells epitaxially grown on silicon by SSMBE using a superlattice and dislocation filters. , 2016, , .		5
68	Optimizations of Defect Filter Layers for 1.3- μm InAs/GaAs Quantum-Dot Lasers Monolithically Grown on Si Substrates. IEEE Journal of Selected Topics in Quantum Electronics, 2016, 22, 50-56.	2.9	69
69	Monolithically Integrated InAs/GaAs Quantum Dot Mid-Infrared Photodetectors on Silicon Substrates. ACS Photonics, 2016, 3, 749-753.	6.6	63
70	Al _{0.2} Ga _{0.8} As Solar Cells Monolithically Grown on Si and GaAs by MBE for III-V/Si Tandem Dual-junction Applications. Energy Procedia, 2016, 92, 661-668.	1.8	9
71	Silicon-based III-V quantum dot devices for silicon photonics. , 2016, , .		0
72	InAs/GaAs quantum-dot light emitters monolithically grown on Si substrate. , 2016, , .		0

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73	Si-Doped InAs/GaAs Quantum-Dot Solar Cell With AlAs Cap Layers. IEEE Journal of Photovoltaics, 2016, 6, 906-911.	2.5	16
74	In situ annealing enhancement of the optical properties and laser device performance of InAs quantum dots grown on Si substrates. Optics Express, 2016, 24, 6196.	3.4	26
75	Electrically pumped continuous-wave III-V quantum dot lasers on silicon. Nature Photonics, 2016, 10, 307-311.	31.4	665
76	InAs/InGaP quantum dot solar cells with an AlGaAs interlayer. Solar Energy Materials and Solar Cells, 2016, 144, 96-101.	6.2	21
77	InAs/GaAs quantum dot lasers monolithically grown on silicon for silicon photonics. , 2016, , .		0
78	Silicon-based III-V quantum-dot lasers for silicon photonics. , 2016, , .		0
79	Monolithically Grown Superluminescent Diodes on Germanium and Silicon substrates. , 2015, , .		0
80	Optimisation of 1.3- μ m InAs/GaAs Quantum-Dot Lasers Monolithically Grown on Si Substrates. Journal of Physics: Conference Series, 2015, 619, 012011.	0.4	1
81	Dislocation filters in GaAs on Si. Semiconductor Science and Technology, 2015, 30, 114004.	2.0	40
82	Long-Wavelength InAs/GaAs Quantum-Dot Light Emitting Sources Monolithically Grown on Si Substrate. Photonics, 2015, 2, 646-658.	2.0	10
83	Optimisation of the dislocation filter layers in 1.3- μ m InAs/GaAs quantum-dot lasers monolithically grown on Si substrates. IET Optoelectronics, 2015, 9, 61-64.	3.3	23
84	Continuous-wave emission of III-V quantum dot lasers grown directly on Si substrates. , 2015, , .		0
85	Effect of rapid thermal annealing on InAs/GaAs quantum dot solar cells. IET Optoelectronics, 2015, 9, 65-68.	3.3	14
86	Quantum Dot Lasers on Silicon by Direct Epitaxial Growth. , 2015, , .		0
87	Electrically Pumped 1.3- μ m InAs/GaAs Quantum Dot Laser Monolithically Grown on Si Substrate Lasing up to 111 $^{\circ}$ C. , 2015, , .		1
88	InAs/GaAsSb quantum dot solar cells. Optics Express, 2014, 22, A679.	3.4	43
89	1.3- μ m InAs/GaAs Quantum-Dot Laser Monolithically Grown on Si Substrates Using InAlAs/GaAs Dislocation Filter Layers. , 2014, , .		2
90	1.3- μ m InAs/GaAs quantum-dot lasers monolithically grown on Si substrates using InAlAs/GaAs dislocation filter layers. Optics Express, 2014, 22, 11528.	3.4	125

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91	InAs/GaAs quantum-dot superluminescent diodes monolithically grown on a Ge substrate. Optics Express, 2014, 22, 23242.	3.4	14
92	1.3 μ m InAs/GaAs quantum-dot laser monolithically grown on Si substrates operating over 100 $^{\circ}$ C. Electronics Letters, 2014, 50, 1467-1468.	1.0	81
93	Submonolayer InGaAs/GaAs quantum dot solar cells. Solar Energy Materials and Solar Cells, 2014, 126, 83-87.	6.2	43
94	Voltage recovery in charged InAs/GaAs quantum dot solar cells. Nano Energy, 2014, 6, 159-166.	16.0	61
95	Electrically pumped continuous-wave 1.3 μ m InAs/GaAs quantum dot lasers monolithically grown on Si substrates. IET Optoelectronics, 2014, 8, 20-24.	3.3	19
96	InAs/GaAs Quantum-Dot Superluminescent Light-Emitting Diode Monolithically Grown on a Si Substrate. ACS Photonics, 2014, 1, 638-642.	6.6	66
97	Design rules for dislocation filters. Journal of Applied Physics, 2014, 116, .	2.5	55
98	Wafer-Scale Fabrication of Self-Catalyzed 1.7 eV GaAsP Core-Shell Nanowire Photocathode on Silicon Substrates. Nano Letters, 2014, 14, 2013-2018.	9.1	58
99	Self-Catalyzed Ternary Core-Shell GaAsP Nanowire Arrays Grown on Patterned Si Substrates by Molecular Beam Epitaxy. Nano Letters, 2014, 14, 4542-4547.	9.1	48
100	Antimony mediated growth of high-density InAs quantum dots for photovoltaic cells. Applied Physics Letters, 2013, 103, 043901.	3.3	20
101	Long-wavelength III-V quantum-dot lasers monolithically grown on Si substrates. , 2013, , .		1
102	InAs/GaAs Quantum-Dot Lasers Monolithically Grown on Si, Ge, and Ge-on-Si Substrates. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1901107-1901107.	2.9	93
103	InAs/GaAs quantum-dot lasers and detectors on silicon substrates for silicon photonics. , 2013, , .		1
104	III-V quantum-dot laser growth on silicon and germanium. , 2013, , .		0
105	Continuous-wave InAs/GaAs quantum-dot laser diodes monolithically grown on Si substrate with low threshold current densities. Optics Express, 2012, 20, 22181.	3.4	153
106	Silicon-based long-wavelength III-V quantum-dot lasers. , 2012, , .		2
107	GaAs Compounds Heteroepitaxy on Silicon for Opto and Nano Electronic Applications. , 0, , .		1